

High Dynamic Range GaAs HBT Amplifier, 50 - 450 MHz

V 1A.00

Advanced

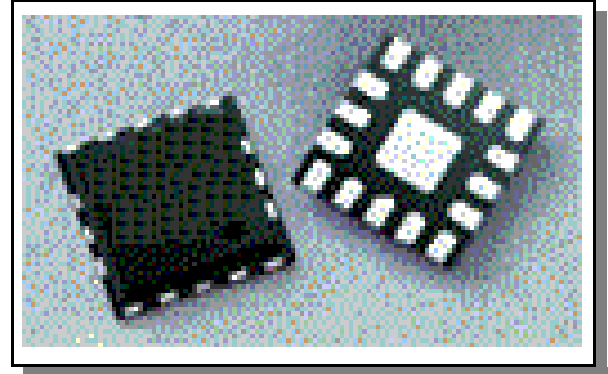
MAAMSS0006

Features

- Greater than 40 dBm Output IP3
- Greater than 20 dBm P1dB
- GaAs iHBT Technology
- Chip Scale Leadless Package
- Single Positive Supply Voltage

Description

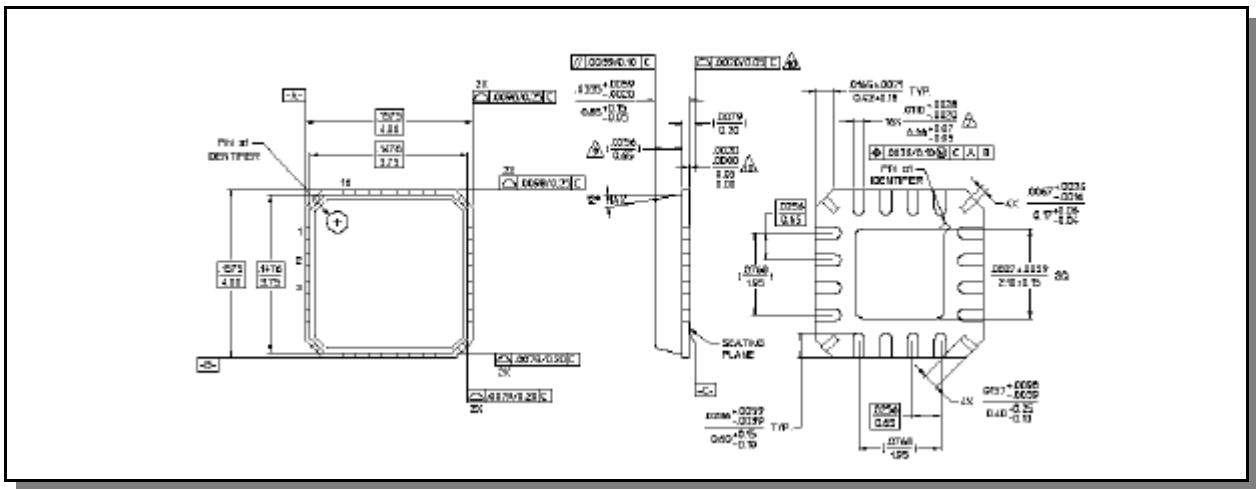
M/A-COM's MAAMSS0006 Amplifier is a high linearity and high efficiency GaAs Heterojunction Bipolar Transistor (HBT) MMIC in a 3mm plastic surface mount package. It is ideal for receiver and transmission applications due to its low noise figure and high OIP3. The MAAMSS0006 is particularly useful in applications requiring high linearity.



Electrical Specifications: $T_A = 25^\circ\text{C}$, $Z_0 = 50\Omega$

Parameter	Test Conditions	Frequency	Units	Min	Typ	Max
Gain		50 - 450 MHz	dB	—	13	—
Return Loss		50 - 450 MHz	dB	—	12	—
Output IP3		50 - 450 MHz	dBm	—	40	—
Output P1dB		50 - 450 MHz	dBm	—	24	—
Supply Voltage		50 - 450 MHz	V	—	5	—
Supply Current		50 - 450 MHz	mA	—	100	—

3mm FQFP-N Package



This Advanced Data Sheet contains technical information about a product M/A-COM may introduce. Specifications subject to change prior to formal introduction. All measurements in a 50 Ohm System.